

isc Silicon NPN Power Transistors
2SC3298/A/B
DESCRIPTION

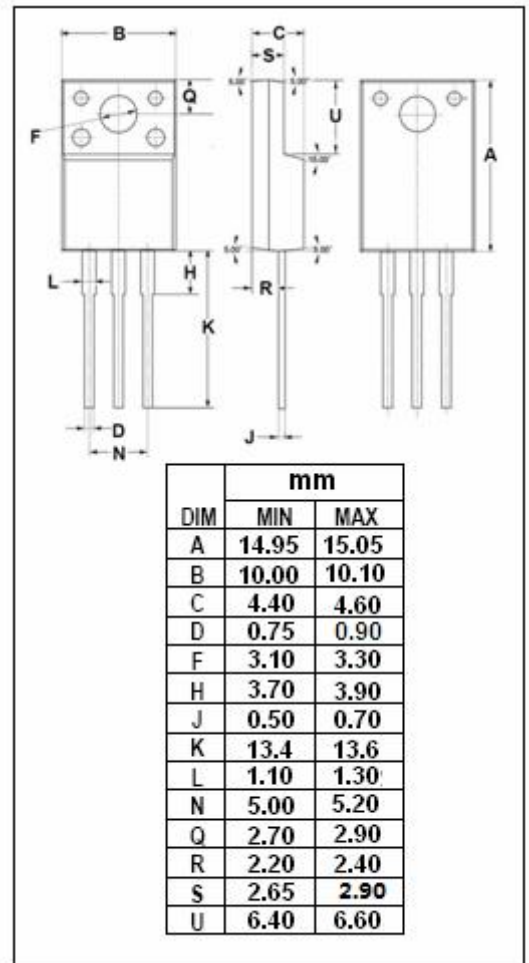
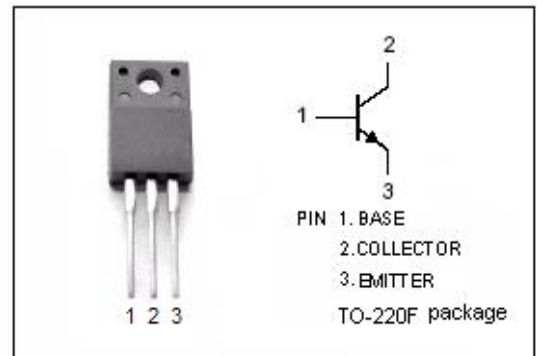
- Good Linearity of h_{FE}
- High Collector-Emitter Breakdown Voltage-
 $V_{(BR)CEO} = 160V(\text{Min})$ -2SC3298
 $= 180V(\text{Min})$ -2SC3298A
 $= 200V(\text{Min})$ -2SC3298B
- Complement to Type 2SA1306/A/B
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Power amplifier applications.
- Driver stage amplifier applications.

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

| SYMBOL | PARAMETER | VALUE | UNIT | |
|-----------|---|----------|------|---|
| V_{CBO} | Collector-Base Voltage | 2SC3298 | 160 | V |
| | | 2SC3298A | 180 | |
| | | 2SC3298B | 200 | |
| V_{CEO} | Collector-Emitter Voltage | 2SC3298 | 160 | V |
| | | 2SC3298A | 180 | |
| | | 2SC3298B | 200 | |
| V_{EBO} | Emitter-Base Voltage | 5 | V | |
| I_C | Collector Current-Continuous | 1.5 | A | |
| I_B | Base Current-Continuous | 0.15 | A | |
| P_C | Collector Power Dissipation @ $T_C=25^\circ\text{C}$ | 20 | W | |
| T_J | Junction Temperature | 150 | °C | |
| T_{stg} | Storage Temperature Range | -55~150 | °C | |



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2SC3298/A/B

ELECTRICAL CHARACTERISTICS

T_c=25°C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|----------------------|--------------------------------------|--|-----|------|-----|------|
| V _{(BR)CEO} | Collector-Emitter Breakdown Voltage | 2SC3298 | 160 | | | V |
| | | 2SC3298A | 180 | | | |
| | | 2SC3298B | 200 | | | |
| | | I _C = 10mA; I _B = 0 | | | | |
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | I _C = 500mA; I _B = 50mA | | | 1.5 | V |
| V _{BE(on)} | Base-Emitter On Voltage | I _C = 500mA; V _{CE} = 5V | | | 1.0 | V |
| I _{CBO} | Collector Cutoff Current | V _{CB} = 160V; I _E = 0 | | | 1.0 | μ A |
| I _{EBO} | Emitter Cutoff Current | V _{EB} = 5V; I _C = 0 | | | 1.0 | μ A |
| h _{FE} | DC Current Gain | I _C = 100mA ; V _{CE} = 5V | 70 | | 240 | |
| f _T | Current-Gain—Bandwidth Product | I _C = 100mA ; V _{CE} = 10V | | 100 | | MHz |
| C _{OB} | Output Capacitance | I _E = 0 ; V _{CB} = 10V; f _{test} = 1.0MHz | | 25 | | pF |

◆ h_{FE} Classifications

| O | Y |
|--------|---------|
| 70-140 | 120-240 |

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